

RELIABILITY REPORT FOR MAX44286xAZS+T

PLASTIC ENCAPSULATED DEVICES

February 24, 2015

MAXIM INTEGRATED

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| Approved by |
|-------------------------|
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| Quality Assurance |
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Conclusion

The MAX44286xAZS+T successfully meets the quality and reliability standards required of all Maxim Integrated products. In addition, Maxim Integrated's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim Integrated's quality and reliability standards.

IV.Die Information

Table of Contents

- I.Device Description
- II.Manufacturing Information
- III.Packaging Information
- V.Quality Assurance Information VI.Reliability Evaluation

.....Attachments

I. Device Description

A. General

The MAX44286 is a zero-drift, high-side current-sense amplifier family that offers precision, low supply current and is available in a tiny 4-bump ultra-thin WLP of 0.78mm x 0.78mm x 0.35mm footprint. This miniature size is of paramount for today's applications in smartphones, mobile accessories, notebooks, portable medical, and all battery-operated portable devices where current monitoring with precision and space are critical. The MAX44286 has voltage output offered in four gain versions of 25V/V, 50V/V, 100V/V, and 200V/V. These four gain versions offer flexibility in the choice of the sense resistor and the very low input offset voltage helps in detecting small currents on the orders of low microamps. Low power capability also offers the possibility of minimizing power dissipation. The MAX44286 operates with a supply voltage range of 1.6V to 5.5V over the -40°C to +85°C temperature range and from 1.8V to 5.5V over the -40°C to +125°C automotive temperature range. Supply voltage for the device is shared with the RS+ pin to fit the MAX44286 in a 4-bump, ultra-thin WLP package.



II. Manufacturing Information

| A. Description/Function: | Low-Power, Precision, 4-Bump WLP, Current-Sense Amplifier |
|--------------------------------|---|
| B. Process: | S18 |
| C. Fabrication Location: | USA |
| D. Assembly Location: | USA |
| E. Date of Initial Production: | November 20, 2014 |

III. Packaging Information

IV. Die Information

| A. Dimensions: | 31.4961 X 31.4961 mils |
|----------------------------|---|
| B. Passivation: | Si ₃ N ₄ /SiO ₂ (Silicon nitride/ Silicon dioxide) |
| C. Interconnect: | AI/0.5%Cu with Ti/TiN Barrier |
| D. Backside Metallization: | None |
| E. Minimum Metal Width: | 0.23 microns (as drawn) |
| F. Minimum Metal Spacing: | 0.23 microns (as drawn) |
| G. Bondpad Dimensions: | |
| H. Isolation Dielectric: | SiO ₂ |
| I. Die Separation Method: | Wafer Saw |



V. Quality Assurance Information

| A. Quality Assurance Contacts: | Don Lipps (Manager, Reliability Engineering) Bryan Preeshl (Vice President of QA) |
|-----------------------------------|---|
| B. Outgoing Inspection Level: | 0.1% for all electrical parameters guaranteed by the Datasheet. 0.1% for all Visual Defects. |
| C. Observed Outgoing Defect Rate: | < 50 ppm |
| D. Sampling Plan: | Mil-Std-105D |

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 80 \times 2}$$
(Chi square value for MTTF upper limit)
(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 13.7 \times 10^{-9}$$

$$\lambda = 13.7 \text{ F.I.T.} (60\% \text{ confidence level @ 25°C})$$

The following failure rate represents data collected from Maxim Integrated's reliability monitor program. Maxim Integrated performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at http://www.maximintegrated.com/qa/reliability/monitor. Cumulative monitor data for the S18 Process results in a FIT Rate of 0.05 @ 25°C and 0.93 @ 55°C (0.8 eV, 60% UCL)

B. E.S.D. and Latch-Up Testing

The OY98-2 die type has been found to have all pins able to withstand an HBM transient pulse of +/-2500V per JEDEC JESD22-A114. Latch-Up testing has shown that this device withstands a current of +/-250mA and overvoltage per JEDEC JESD78.



Table 1 Reliability Evaluation Test Results

MAX44286xAZS+T

| TEST ITEM | TEST CONDITION | FAILURE IDENTIFICATION | SAMPLE SIZE | NUMBER OF FAILURES | COMMENTS |
|--------------------|-----------------|---------------------------|-------------|-----------------------|----------|
| Static Life Test (| Note 1) | | | | |
| | Ta = 135°C | DC Parameters | 80 | 0 | |
| | Biased | & functionality | | | |
| | Time = 192 hrs. | | | | |

Note 1: Life Test Data may represent plastic DIP qualification lots.